

ZXTP2012G

60V PNP MEDIUM POWER LOW SATURATION TRANSISTOR IN SOT223

Features

- BV_{CEO} > -60V
- I_C = -5.5A Continuous Collector Current
- I_{CM} = -15A Peak Pulse Current
- Low Saturation Voltage V_{CE(SAT)} < -70mV Max @ -1A
- R_{SAT} = 39mΩ @ -5A for Low Equivalent On-Resistance
- h_{FE} Specified up to -10A for High Gain Hold Up
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound.
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)

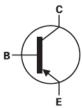
Applications

- DC-DC Converters
- MOSFET Gate Drivers
- Charging Circuits
- Power Switches
- Motor Control

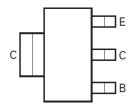
SOT223



Top View



Device Schematic



Pin-Out Top View

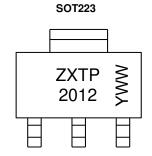
Ordering Information (Note 4)

Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
ZXTP2012GTA	AEC-Q101	ZXTP2012	7	12	1,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



ZXTP 2012 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week code (01 - 53)



Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-100	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	Ic	-5.5	A
Peak Pulse Current	I _{CM}	-15	A

Thermal Characteristics (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	D	3.0 24	W mW/°C	
Linear Derating Factor	(Note 6)	P_{D}	1.6 12.8		
Thermal Resistance, Junction to Ambient	(Note 5)	R _{0JA}	42		
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	78	°C/W	
Thermal Resistance, Junction to Lead (Note 7)		$R_{\theta JL}$	8.8		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 8)

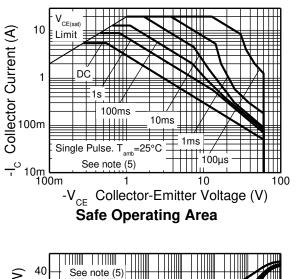
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	V	С

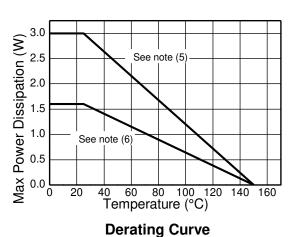
Notes:

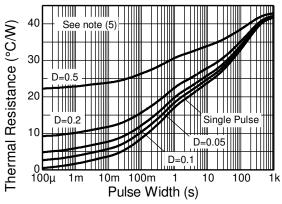
- 5. For a device mounted with the collector lead on 52mm x 52mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air 5. For a device mounted with the collector lead on 32mm x 32mm x 32mm 202 copper that is conditions whilst operating in steady-state.
 6. Same as Note 5, except the device is mounted on 25mm x 25mm 1oz copper.
 7. Thermal resistance from junction to solder-point (at the end of the collector lead).
 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

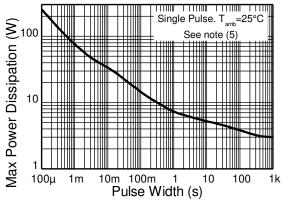


Thermal Characteristics and Derating Information









Transient Thermal Impedance

Pulse Power Dissipation



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-100	-120	_	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage	BV _{CER}	-100	-120		V	$I_C = -1\mu A$, RB $\leq 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	-60	-80	_	V	$I_C = -10mA$
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	-8.1		V	$I_E = -100\mu A$
Collector Cutoff Current	I _{CBO}		< -1 —	-20 -0.5	nA μA	V _{CB} = -80V V _{CB} = -80V, T _A = +100°C
Collector Cutoff Current	I _{CER} R≤1kΩ		< -1 —	-20 -0.5	nA μA	V _{CB} = -80V V _{CB} = -80V, T _A = +100°C
Emitter Cutoff Current	I _{EBO}	_	< -1	-10	nA	V _{EB} = -6V
Collector-Emitter Saturation Voltage (Note 9)	V _{CE(SAT)}	_	-15 -55 -90 -195	-25 -70 -120 -250	mV	$I_C = -0.1A$, $I_B = -10mA$ $I_C = -1A$, $I_B = -100mA$ $I_C = -2A$, $I_B = -200mA$ $I_C = -5A$, $I_B = -500mA$
Base-Emitter Saturation Voltage (Note 9)	V _{BE(SAT)}	_	-1.03	-1.15	V	$I_C = -5A$, $I_B = -500mA$
Base-Emitter Turn-On Voltage (Note 9)	V _{BE(ON)}	_	-0.92	-1.02	V	$I_C = -5A$, $V_{CE} = -1V$
DC Current Gain (Note 9)	h _{FE}	100 100 45 10	250 200 90 25	300	_	$\begin{split} I_{C} &= -10 \text{mA}, \ V_{CE} = -1 \text{V} \\ I_{C} &= -2 \text{A}, \ V_{CE} = -1 \text{V} \\ I_{C} &= -5 \text{A}, \ V_{CE} = -1 \text{V} \\ I_{C} &= -10 \text{A}, \ V_{CE} = -1 \text{V} \end{split}$
Transition Frequency	f _T		120	_	MHz	$V_{CE} = -10V, I_{C} = -100mA,$ f = 50MHz
Output Capacitance (Note 9)	C _{OBO}		48	_	pF	$V_{CB} = -10V$, $f = 1MHz$
Switching Times	t _{ON}	1	39 370		ns	$V_{CC} = -10V, I_C = -1A,$ $I_{B1} = -I_{B2} = 100mA$

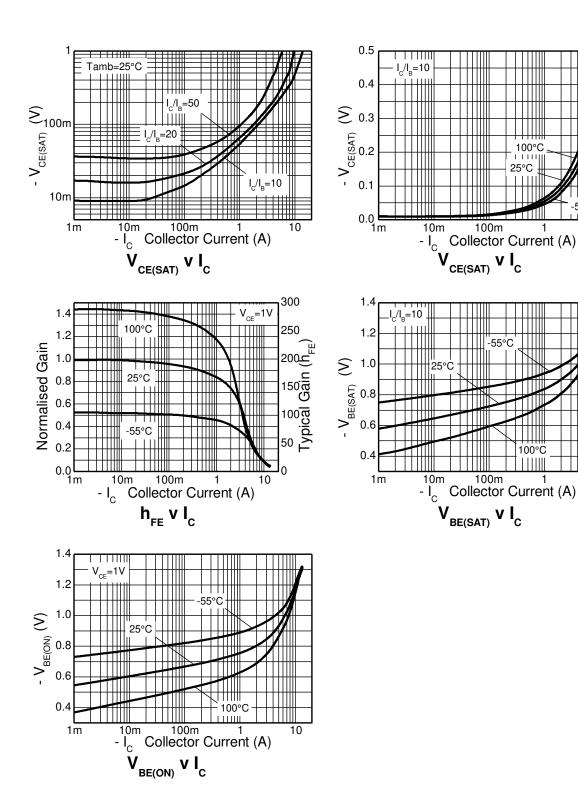
Note: 9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

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Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

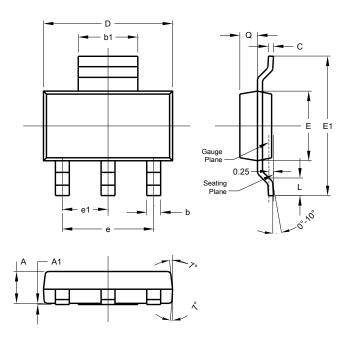




Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

SOT223

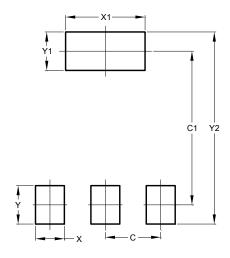


SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A 1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

SOT223



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
C2	8.00



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